2SK4088LS

ON Semiconductor®

N-Channel Power MOSFET 650V, 11A, 0.85Ω, TO-220F-3FS

http://onsemi.com

Features

- · ON-resistance RDS(on)= 0.65Ω (typ.)
- · Input capacitance Ciss=1000pF (typ.)

· 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		650	V
Gate to Source Voltage	V _{GSS}		±30	V
Ducin Comment (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	11	А
Drain Current (DC)	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	7.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	А
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	37	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		65	mJ
Avalanche Current *5	IAV		11	Α

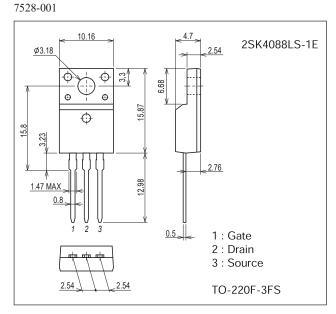
Note:*1 Shows chip capability

- *2 Package limited
- *3 Our condition is radiation from backside.
 - The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.
- *4 VDD=50V, L=1mH, IAV=11A (Fig.1)
- *5 L≤1mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit: mm (typ)

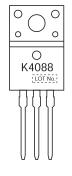


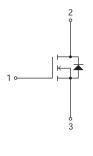
Ordering & Package Information

Device	Package	Shipping	memo
2SK4088LS-1E	TO-220F-3FS, SC-67	50pcs./tube	Pb-Free

Marking

Electrical Connection



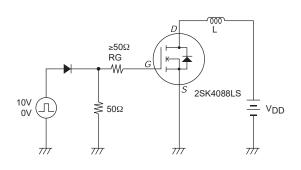


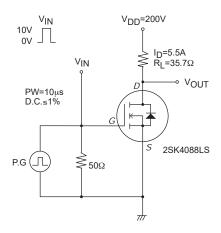
Electrical Characteristics at Ta=25°C

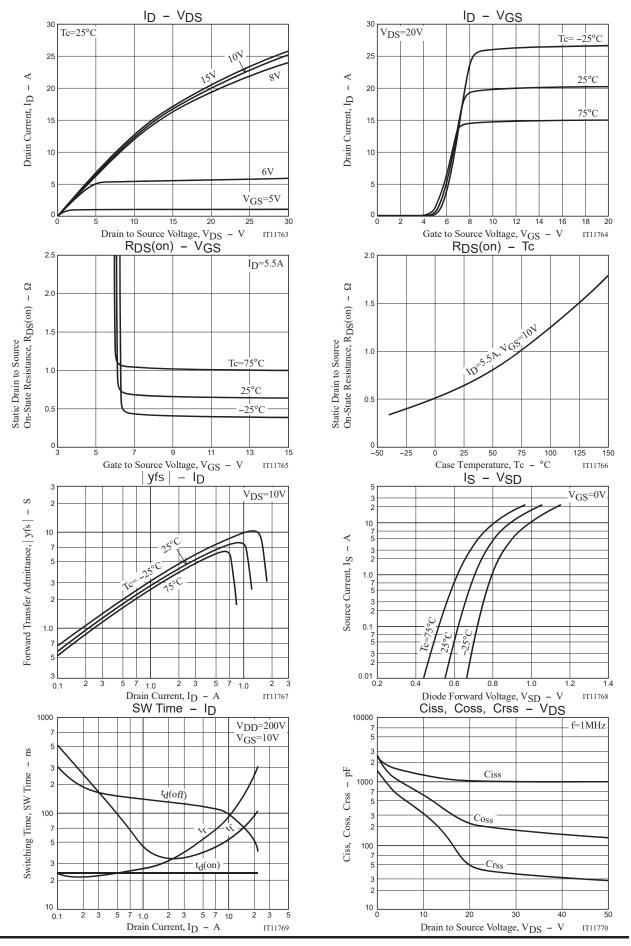
Danamatan	Cbl	0 15:	Ratings			11.2
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	650			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =520V, V _{GS} =0V			100	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5.5A	3.3	6.5		S
Static Drain to Source On-State Resistance	RDS(on)	ID=5.5A, VGS=10V		0.65	0.85	Ω
Input Capacitance	Ciss			1000		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		172		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t _d (on)			24		ns
Rise Time	t _r	Consider the Automotive		58		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		117		ns
Fall Time	tf			40		ns
Total Gate Charge	Qg			37.6		nC
Gate to Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =11A		6.8		nC
Gate to Drain "Miller" Charge	Qgd			17.6		nC
Diode Forward Voltage	V _{SD}	IS=11A, VGS=0V		0.9	1.2	V

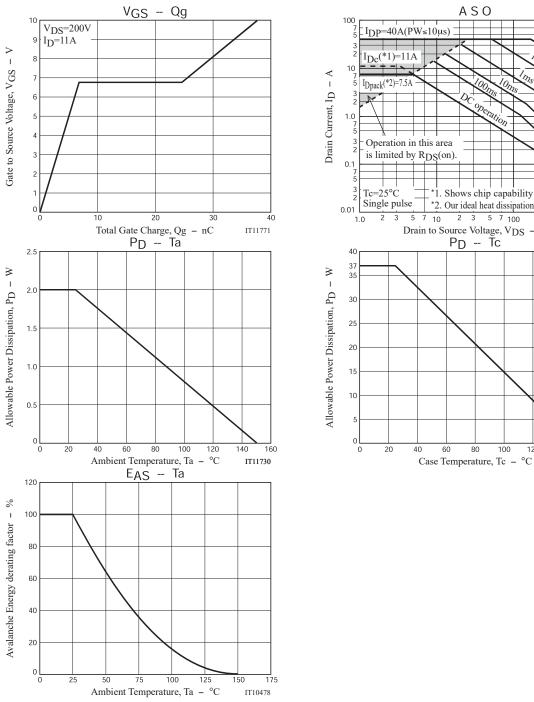
Fig.1 Unclamped Inductive Switching Test Circuit

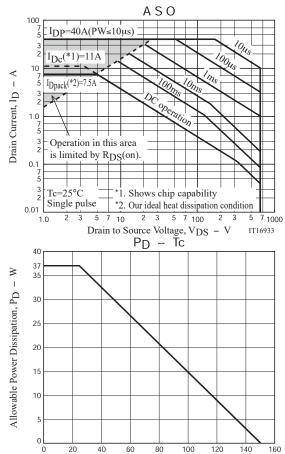
Fig.2 Switching Time Test Circuit











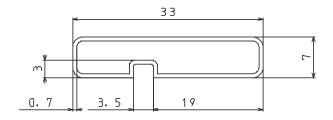
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Magazine Specification

2SK4088LS-1E

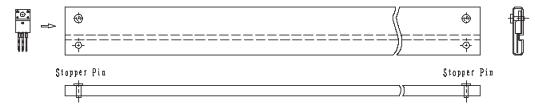
1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (pos				format
1111161 111111	102042120 14222		Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3F\$	TO-220F	50	1, 000	4.000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

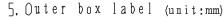


 $\begin{array}{lll} Tolerance=\pm (), \ 3mm \\ Thickness=(), \ 7\pm (), \ 2mm \\ Length & =532, \ 5\pm 2mm \\ Material & =PVC \ (Antistatic \ treatment) \end{array}$

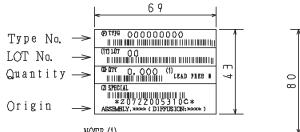
3. Storage method to magazine

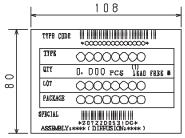


4. Inner box label (unit:mm)



It is a label at the time of factory shigments. The form of a label may change in physical distribution process.





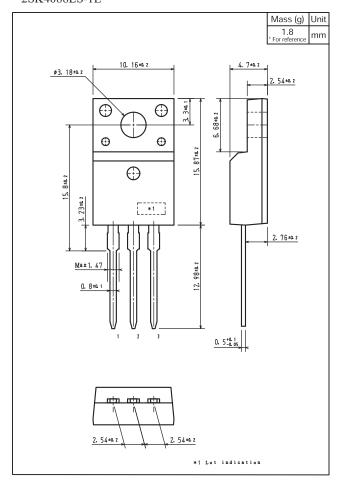
NOTE(1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK4088LS-1E



Note on usage: Since the 2SK4088LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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